

AMENDMENT UNDER 37 C.F.R. § 1.111  
U. S. Application No. 09/659,456

range of 1 to 10 watts and the laser apparatus generates output power up to several watts in a stable fundamental transverse mode.

57. (New) A laser apparatus according to claim 1, wherein the GaN-based compound in the first active layer of the semiconductor laser element is an InGaN material for emitting an *A'* excitation light in the 410 nm band, the surface-emitting semiconductor element further comprises a GaN substrate, and the first laser light is supplied to the surface-emitting semiconductor laser element through the GaN substrate.

58. (New) A laser apparatus according to claim 28, wherein the GaN-based compound in the first active layer of the semiconductor laser element is an InGaN material for emitting an excitation light in the 410 nm band, the surface-emitting semiconductor element further comprises a GaN substrate, and the first laser light is supplied to the surface-emitting semiconductor laser element through the GaN substrate.

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